

Title of Change:	KAE-02150 datasheet: Recommend non-use of temperature diode, plus clarification regarding Sampling	
	Plan	
Effective date:	15 March 2018	
Contact information:	Contact your local ON Semiconductor Sales Office or <john.frenett@onsemi.com></john.frenett@onsemi.com>	
Type of notification:	This Product Bulletin is for notification purposes only. ON Semiconductor will proceed with implementation of this change upon publication of this Product Bulletin.	
Change category:	Wafer Fab Change Assembly Change Test Change Documentation	
Change Sub-Category(s): Manufacturing Site Change/Au Manufacturing Process Chang		
Sites Affected:	ON Semiconductor Sites:External Foundry/Subcon Sites:ON Rochester, New YorkNone	
Description and Purpose:		
A temperature sensing diode was provided on-chip, intended to serve as a secondary or backup source for die temperature. (The primary source for die temperature is a thermistor.) ON Semiconductor has determined that temperature readings from the diode are unreliable (inaccurate). The temperature sensing diode will remain on-chip. However, ON Semiconductor will remove text describing the diode from KAE-02150's		
datasheet. Also, the pinout table which references the temperature sensing diode pin will be updated to show a ground bias for the pin.		
To date, there have been no indications of use of the temperature sensing diode by KAE-02150 customers. Customers have been using the thermistor, often in conjunction with a closed loop controller.		
Regarding the Sampling Plan column of Table 7 (SPECIFICATIONS), entries for Photodiode Dark Current (Average) and Vertical CCD Dark Current change from Die to Design . Die would imply that each part produced is tested; in fact, testing was done via characterization associated with product commercialization.		
Another change to Table 7 (SPECIFICATIONS), also involving Photodiode Dark Current (Average) , is a change in the maximum value. The former value of 70 was a mistaken carryover. The new value of 3 is closely linked to demonstrated manufacturing capability.		
Details:		
 Table 4 (PIN DESCRIPTION) has been updated as follows: a. H01's Label was TD; now reads GND. b. H01's Description was Temperature Diode Sensor; now reads Ground. Table 5 (PGA WITH INTEGRATED TEC PIN DESCRIPTION) includes the following changes: a. H01's Label was N/C; now reads GND b. H01's Description was No Connection; now reads Ground. Table 7 (SPECIFICATIONS) has been updated: a. Photodiode Dark Current (Average) was 70 e/p/s; now reads 3 e/p/s b. Photodiode Dark Current (Average) had Sampling Plan designated as Die; now reads Design c. Vertical CCD Dark Current had Sampling Plan designated as Die; now reads Design 		
The change will not impact form, fit, or function of KAE-02150 image sensors. That is, neither the die nor finished assembly are changing.		



List of Affected Standard Parts:

KAE-02150-ABB-JP-FA KAE-02150-ABB-JP-FA KAE-02150-FBB-JP-FA KAE-02150-ABB-SP-FA KAE-02150-ABB-SP-FA KAE-02150-ABB-SP-FA KAE-02150-FBB-SP-FA KAE-02150-ABB-SD-FA KAE-02150-ABB-SD-FA KAE-02150-FBB-SD-FA

Appendix A: Changed Products

Product	Customer Part Number
KAE-02150-ABB-JP-FA	
KAE-02150-FBB-JP-FA	